

Data Sheet

Version 1.4/May 2022 ML-2664-2718-DB1Z1



拥有核心芯片技术的MEMS传感技术公司

A MEMS Sensor Company with Advanced Core Chip Technology



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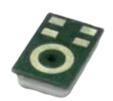




Product Specification

ML-2664-2718-DB1Z1 Bottom-port digital silicon microphone





Description

ML-2664-2718-DB1Z1 is a miniature digital bottom-port silicon microphone that receives the sound signal from the backside hole on PCB. By using our own innovative and unique MEMS microphone chip design, SV Senstech provides a series of packaged MEMS silicon microphones with compact size to achieve excellent performance such as high SNR, high AOP, excellent reliability and broadband frequency response. This series of MEMS microphones find wide applications in Laptops, automotives, cell phones, TWS, wearable devices and other portable electronic devices.

Features

- \triangleright Compact size of 2.75 \times 1.85 \times 0.95 mm³
- \triangleright Sensitivity of -26dBFS (±1dBFS)
- ➤ High signal-to-noise ratio of 64 dB
- Extreme low THD of 0.1% at 94 dB SPL
- ➤ PDM Output

- ➤ High immune to RF/EM interference
- > High mechanical strength
- > High temperature resistance
- > Excellent reliability



Applications

Laptops, automotives, smartphones, Bluetooth headsets/headphones, TWS, wearable electronics, IoT related devices, etc.



Absolute maximum ratings

Parameter	Absolute Maximum Rating	Units
Vdd, DATA to Ground	-0.3, +5.0	V
CLOCK to Ground	-0.3, +5.0	V
SELECT to Ground	-0.3, +5.0	V
Input Current	±5	mA
Short Circuit to/from DATA	Indefinite to Ground or Vdd	sec
Temperature	-40 to +100	°C

Notes:

- 1) Stresses exceeding these "Absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only.
- 2) Functional operation at these or any other conditions beyond those indicated under "Acoustic and electrical specifications" is not implied.
- 3) Exposure beyond those indicated under "Acoustic and electrical specifications" for extended periods may affect device reliability.



Acoustic and electrical specifications

General Microphone Specifications

Test conditions: $23^{\circ}\text{C}\pm2^{\circ}\text{C}$, $55\%\pm5\%$ R.H., VDD=1.8V, Fclock=2.4 MHz, SELECT grounded, no load, 100nF capacitor between VDD and GND, unless otherwise indicated

Parameter		Symbol	Condition	Min.	Тур.	Max	Unit
Supply Volta	age	Vdd		1.6		3.6	V
Sleep Curre	nt	Isleep	Fclock≤1kHz		32	42	μA
	Sleep Mode	Fclock		0		50	kHz
Clock Frequency Range	Low Power Mode	Fclock		150	768	900	kHz
Range	Normal Mode	Fclock		1.024	2.4	4.8	MHz
Clock Duty	Cycle			40 50 60			%
Directivity				Omnidirectional			nal
Data Format				1/2 Cycle 1-bit PDM			t PDM
Output Load		Cload				140	pF
Fall Asleep	Time	Tslp	Fclock≤50kHz		5		μs
Wake-up Tim	e	Twk	Fclock>150kHz		30		μs
Power-up Ti	me	Tpu		35 μs			μs
Mode Change	Time	Ттс		10 μs			μs
Dimension				2.75×1.85×0.95 mm ³			mm ³
Directivity				Omnidirectional			
Frequency R	esponse	F			20~10k		Hz

Normal Mode

Test conditions: $23^{\circ}\text{C}\pm2^{\circ}\text{C}$, $55\%\pm5\%$ R.H., VDD=1.8V, Fclock=2.4 MHz, SELECT grounded, no load, 100nF capacitor between VDD and GND, unless otherwise indicated

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Sensitivity	Sens	94dB SPL @1kHZ	-27	-26	25	dBFS
Signal to Noise Ratio	SNR	94dB SPL @1kHZ, A-weighted, Fclock=2.4MHz		64		dB (A)



Current Consumption	Idd	Vdd=1.8V, fclock=2.4MHz	600		1050	μA
Total Harmonic Distortion	THD	94 dB SPL @ 1kHz		0. 1		%
Acoustic Overload Point	AOP	10% THD @ 1kHz		120		dBSPL
Power Supply Rejection	PSR	100mVpp square wave @ 217 Hz, A-weighted		-90		dBFS (A)
Power Supply Rejection Ratio	PSRR	200mVpp sine wave @1kHz		60		dBV/FS

Low-Power Mode

Test conditions: $23^{\circ}\text{C}\pm2^{\circ}\text{C}$, $55\%\pm5\%$ R.H., VDD=1.8V, Fclock=768kHz, SELECT grounded, no load, 100nF capacitor between VDD and GND, unless otherwise indicated

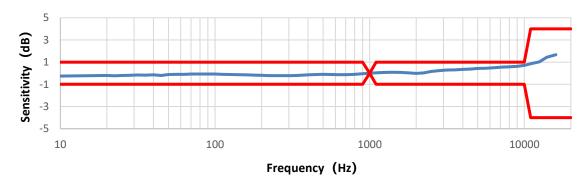
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Sensitivity	Sens	94dB SPL @1kHz	-27	-26	-25	dBFS
Signal to Noise Ratio	SNR	94dB SPL @1kHz, A-weighted (BW=8kHz)		63		dB (A)
Current Consumption	Idd			300	350	μA
Total Harmonic Distortion	THD	94 dB SPL @1kHz		0.1		%
Acoustic Overload Point	AOP	10% THD @1kHz		120		dBSPL
Power Supply Rejection	PSR	100mVpp square wave @ 217 Hz, A-weighted		-90		dBFS (A)
Power Supply Rejection Ratio	PSRR	200mVpp sine wave @1kHz		60		dBV/FS



• Microphone interface specifications

Parameter	Symbol		Unit		
rarameter	Буш БО1	Min	Туре	Max	OHIT
Logic input High	V_{ih}	$0.65 \times VDD$		VDD+0.3	V
Logic input Low	V_{i1}	-0.3		$0.35 \times VDD$	V
Logic Output High	$ m V_{oh}$	VDD-0.45			V
Logic Output Low	V_{ol}			0.45	V
Clock Duty Cycle		40		60	%

Frequency response

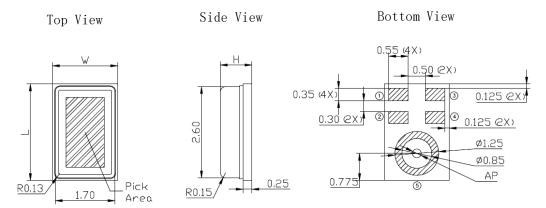


Hz	10	20	100	900	1000	1100	3000	5000	8000	10000
USL	1	1	1	1	0	1	1	1	1	1
LSL	-1	-1	-1	-1	0	-1	-1	-1	-1	-1

Figure 1. Typical free field frequency response (normalized to 1 kHz)



Mechanical specifications

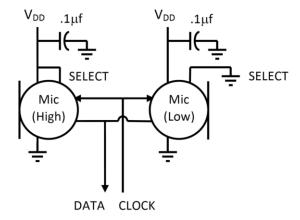


Dimension						
Item	Dimension	Tolerance				
Length(L)	2.75 mm	±0.1 mm				
Width(W)	1.85 mm	±0.1 mm				
Height(H)	0.95 mm	±0.1 mm				
AP	ф 0. 25mm	±0.05 mm				

Pin #	Pin Name
1)	VDD
2	CLOCK
3	DATA
4	SELECT
(5)	GND

Figure 2. Detailed mechanical drawings

Interface circuit

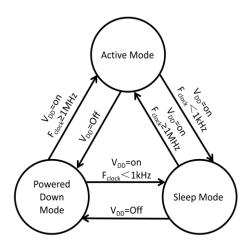


Microphone	SELECT	Asserts DATA On	Latch DATA On
Mic (High)	V_{DD}	Rising Clock Edge	Falling Clock Edge
Mic (Low)	GND	Falling Clock Edge	Rising Clock Edge

Place 100nF decoupling capacitor between VDD and GND, and place this capacitor as near to microphone's VDD PIN as possible.

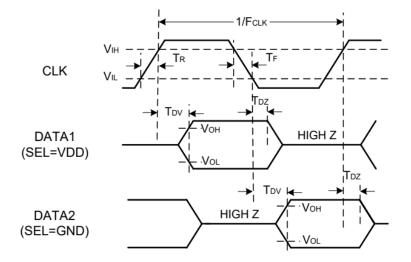


• Device state diagram

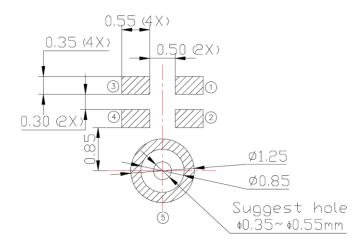


• Time diagram

Parameter	Symbol	Min	Тур	Max	Conditions
Time required for data valid on the rising edge clock	${ m t}_{ m dvr}$	24 ns		48 ns	$R_L=1$ M Ω , $C_L=12$ pF
Time required for data valid on the falling edge clock	$t_{ m dvf}$	24 ns		48 ns	$R_L=1$ M Ω , $C_L=12$ pF
Time required for data to be Z	$t_{ m dz}$	0 ns		20 ns	$R_L=1$ M Ω , $C_L=12$ pF



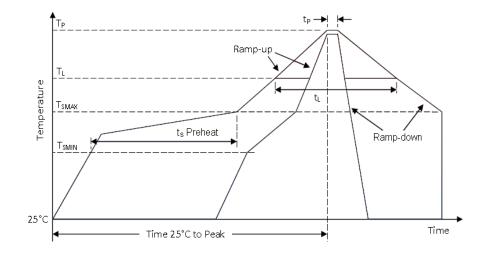
Example land pattern



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Figure 3. Recommended landing pattern on customers' PCB

Recommended reflow profile





D	Parameter (lead-free)	
Average temperature chan	ge rate $(T_{SMAX}$ to $T_P)$	3ºC/second max.
Preheat	$ \begin{array}{c} \text{Minimum temperature } (T_{\text{SMIN}}) \\ \text{Maximum temperature } (T_{\text{SMAX}}) \\ \text{Time } (T_{\text{SMIN}} \text{ to } T_{\text{SMAX}}) \end{array} (t_s) $	150°C 200°C 60-180 seconds
Reflow		217°C 60-150 seconds
Peak temperature	Temperature (T_P) Time (t_P)	260°C 20-40 seconds
Cooling rate $(T_P \text{ to } T_{SMAX})$	6ºC/second max	
Time required from 25°C to peak temperature		8 minutes max

Figure 4. Recommended leadless solder reflow temperature profile

Notes:

- 5) The air blow speed during reflow process should be low to avoid impurity entering the acoustic hole during reflow process.
- 6) Do not wash or clean the product to avoid impurity entering the product.
- 7) Do not carry out the reflow process more than 5 times. If the melting point of solders is lower, the peak temperature should be accordingly reduced.

Reliability specifications

Test Item	Description	
Temperature/Humidity Bias	1,000 hours at +85°C/85% R.H. under bias (JESD22-A101A-B)	
Thermal shock	100 cycles air-to-air thermal shock from -40°C to +125°C with 15minute soaks. (IEC 68-2-4)	
High Temperature Storage	1,000 hours at +105°C environment(IEC 68-2-2)	
Low Temperature Storage	1,000 hours at -40°C environment(IEC 68-2-1)	
High Temperature Bias	1,000 hours at +105℃ under bias(IEC 68-2-2)	
Low Temperature Bias	1,000 hours at -40℃ under bias(IEC 68-2-1)	
Drop test	Using 150g fixture, 3 drops along each of 6 axes from 1.5m height onto slippery marble floor(IEC 68-2-27)	
ESD-HBM	3 discharges of ± 2 kV direct contact to I/O pins. (MIL 883E, Method 3015.7)	
ESD-LID/GND	3 discharges of ± 8 kV direct contact to lid while unit is grounded. (IEC 61000-4-2)	
ESD-MM	3 discharges of ± 200 V direct contact to I/O pins. (ESD STM5.2)	

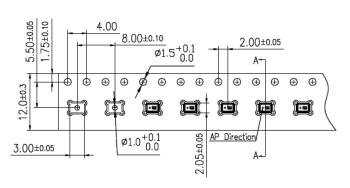


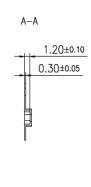
Vibration test	4 cycles of 20 to 2,000 Hz sinusoidal sweep with 20 G peak acceleration lasting 12 minutes in X, Y, and Z directions (Mil-Std-883E, Method 2007.2 A)		
Reflow test	5 reflow cycles with peak temperature of +260℃		
Mechanical Shock	3 pulses of 10,000 G in the X, Y, and Z direction (IEC 68-2-27, Test Ea)		

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Notes: After reliability tests are performed, the sensitivity of the microphones shall not deviate more than 3 dB from its initial value. After 3 reflow cycles, the sensitivity of the microphone shall not deviate more than 3dB from its initial value.

Packaging and marking detail





Model Number	Reel Diameter	Quantity Per Reel	Quantity Per Carton
ML-2664-2718-DB1Z1	13"	5,000	5,000 * 10 = 50,000Pcs

Notes:

- 1) Dice are packaged in black carrier band which uses anti-electrostatic material. Each volume of packaged products is 5000 pcs.
- 2) The space between two dice is 8mm packaged in the carrier band with 12-mm width rolled in the reel of 13-inch diameter.
- 3) The package requirements mentioned below is the company's standard delivery specifications.

 If you need special packages, please contact our sales staff.
- 4) All dimensions are in millimeters (mm) with tolerance of \pm 0.3mm.



Materials statement

- > Meets the requirements of the European RoHS directive 2011/65/EC as amended.
- > Meets the requirements of the industry standard IEC 61249-2-21:2003 for halogenated substances and SV SensTech Green Materials Standards Policy section on Halogen-Free.

Remarks

- > MSL (moisture sensitivity level) Class 1.
- Maximum of 3 reflow cycles is recommended.
- In order to minimize device damage:
 - Do not board wash or clean after the reflow process.
 - Do not brush board with or without solvents after the reflow process.
 - Do not directly expose to ultrasonic processing, welding, or cleaning.
 - Do not insert any object in the port hole of device at any time.
 - Do not apply over 30 psi of air pressure into the port hole.
 - Do not pull a vacuum over the port hole of microphone.
 - Do not apply a vacuum when repacking into sealed bags at a rate faster than 0.5 atm/sec.

Version updates

Version	Updated Content	Updated Date
1.0	Initial release	2021-07-29
1.1	Update FR Limit	2021-08-31
1.2	Logo change	2021-12-29
1.3	Update Time diagram	2022-03-11
1.4	Update Reliability specifications	2022-5-17

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